

MNLM113-1-X REV 2A1

 Original Creation Date: 11/07/96
 Last Update Date: 06/03/02
 Last Major Revision Date: 05/14/02

REFERENCE DIODE
General Description

The LM113 is a temperature compensated, low voltage reference diode. It features extremely-tight regulation over a wide range of operating currents in addition to an unusually-low breakdown voltage and good temperature stability.

The diode is synthesized using transistors and resistors in a monolithic integrated circuit. As such, it has the same low noise and long term stability as modern IC op amps. Further, output voltage of the reference depends only on highly-predictable properties of components in the IC; so they can be manufactured and supplied to tight tolerances.

The characteristics of this reference recommend it for use in bias-regulation circuitry, in low-voltage power supplies or in battery powered equipment. The fact that the breakdown voltage is equal to a physical property of silicon—the energy-band gap voltage—makes it useful for many temperature-compensation and temperature-measurement functions.

Industry Part Number

LM113

Prime Die

LM113

NS Part Numbers

 LM113-1H-QMLV
 LM113-1H-SMD
 LM113-1WG-QMLV
 LM113-1WG-SMD

Controlling Document

SEE FEATURES SECTION

Processing

MIL-STD-883, Method 5004

Quality Conformance Inspection

MIL-STD-883, Method 5005

Subgrp Description Temp (°C)

1	Static tests at	+25
2	Static tests at	+125
3	Static tests at	-55
4	Dynamic tests at	+25
5	Dynamic tests at	+125
6	Dynamic tests at	-55
7	Functional tests at	+25
8A	Functional tests at	+125
8B	Functional tests at	-55
9	Switching tests at	+25
10	Switching tests at	+125
11	Switching tests at	-55

Features

- Low breakdown voltage: 1.220V
- Dynamic impedance of 0.3 Ohms form 500uA to 20mA
- Temperature stability typically 1% over -55 C to 125 C range

CONTROLLING DOCUMENTS:

LM113-1H-QMLV	5962-9684302VXA
LM113-1H-SMD	5962-8671102XA
LM113-1WG-QMLV	5962-9684302VZA
LM113-1WG-SMD	5962-8671102ZA

(Absolute Maximum Ratings)

(Note 1)

Power Dissipation (Note 2)		100 mW
Reverse Current		50 mA
Forward Current		50 mA
Storage Temperature Range		-65 C ≤ Ta ≤ +150 C
Lead Temperature (Soldering, 10 seconds)		300 C
Operating Temperature Range		-55 C ≤ Ta ≤ + 125 C
Maximum Junction Temperature		+150 C
Thermal Resistance		
ThetaJA		
METAL CAN	(Still Air)	440 C/W
	(500LF/Min Air Flow)	TBD
CERAMIC SOIC	(Still Air)	218 C/W
	(500LF/Min Air Flow)	140 C/W
ThetaJC		
METAL CAN		80 C/W
CERAMIC SOIC		27 C/W
ESD Tolerance (Note 3)		4000V

Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions.

Note 2: The maximum power dissipation must be derated at elevated temperatures and is dictated by Tjmax (maximum junction temperature), ThetaJA (package junction to ambient thermal resistance), and TA (ambient temperature). The maximum allowable power dissipation at any temperature is Pdmax = (Tjmax - Ta) / ThetaJA or the number given in the Absolute Maximum Ratings, whichever is lower.

Note 3: Human body model, 1.5K Ohms in series with 100pF.

Electrical Characteristics

DC PARAMETERS

SYMBOL	PARAMETER	CONDITIONS	NOTES	PIN-NAME	MIN	MAX	UNIT	SUB-GROUPS
Vzr	Zener Voltage	Ir = 1 mA			1.210	1.232	V	1
					1.206	1.234	V	2, 3
Delta Vzr	Delta Zener Voltage	0.5mA <= Ir <= 20mA				15	mV	1
		0.5mA <= Ir <= 10mA				15	mV	2, 3
Vf	Forward Voltage Drop	If = 1mA				1	V	1, 2, 3
Rr	Reverse Dynamic Impedance	Ir = 1mA	1			1	Ohm	4
		Ir = 10mA	1			0.8	Ohm	4

DC PARAMETERS: DRIFT VALUES

(The following conditions apply to all the following parameters, unless otherwise specified.)

DC: Delta calculations performed on JAN S and QMLV devices at Group B, Sugroup 5 "ONLY".

Vzr	Zener Voltage	Ir = 1mA			-0.02	0.02	V	1
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Note 1: Guaranteed parameter not tested.

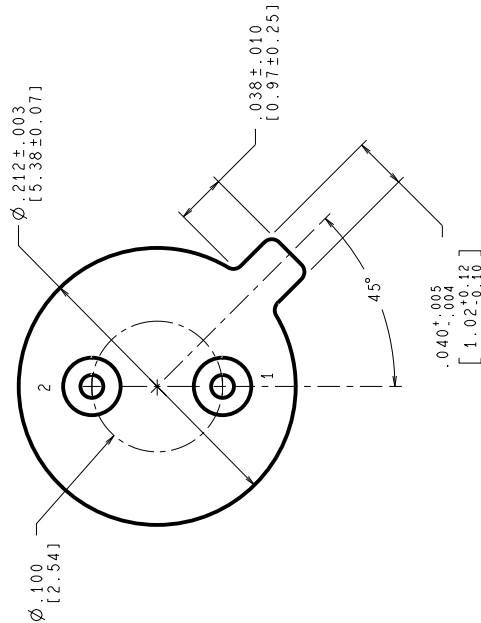
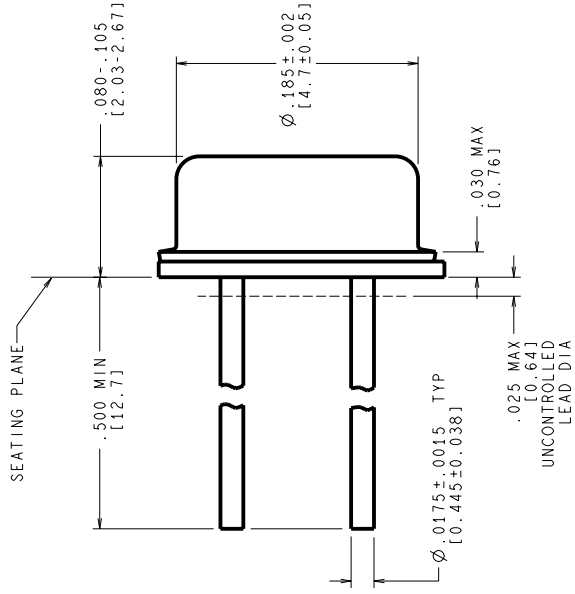
Graphics and Diagrams

GRAPHICS#	DESCRIPTION
06331HRA6	CERAMIC SOIC (WG), 10 LEAD (B/I CKT)
09385HRA1	METAL CAN, TO-46,2LD, .100 DIA P.C. (B/I CKT)
H02ARE	METAL CAN, TO-46,2LD, .100 DIA P.C. (P/P DWG)
P000472A	CERAMIC SOIC (WG), 10 LEAD (PIN OUT)
P000475A	METAL CAN, TO-46,2LD, .100 DIA P.C. (PIN OUT)
WG10ARC	CERAMIC SOIC (WG), 10 LEAD (P/P DWG)

See attached graphics following this page.

REVISIONS

LTR	DESCRIPTION	E.C.N.	DATE	BY/APP'D
D	REVISE & REDRAW PER NEW STANDARD	10402	05/04/1994	TL/GY
E	UPDATE TITLE & MIL/AERO STAMP. CHANGE DWG SIZE FORMAT FROM B TO C.	12131	11/17/1998	MS/



CONTROLLING DIMENSION IS INCH
VALUES IN () ARE MILLIMETERS

MIL-PRF-38535
CONFIGURATION CONTROL

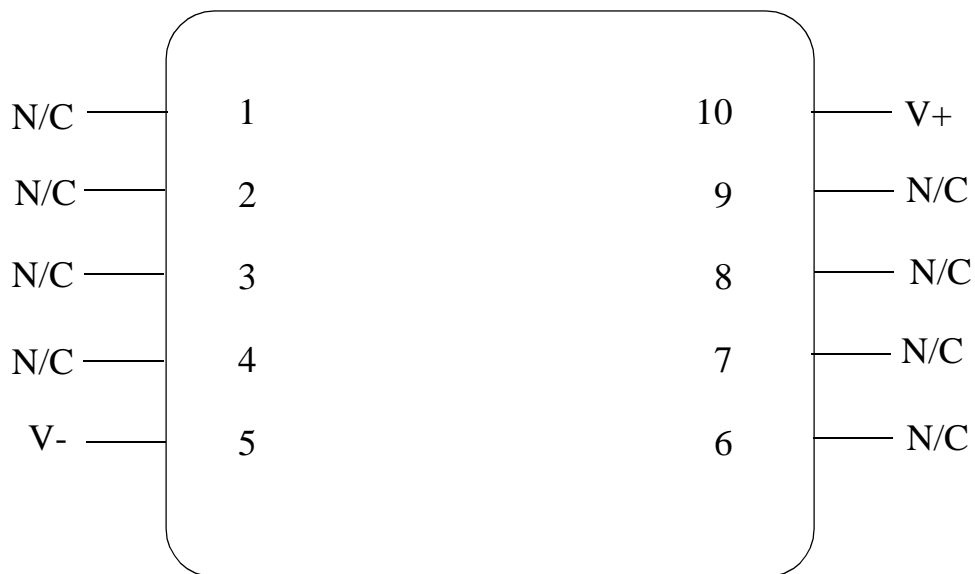
NOTES: UNLESS OTHERWISE SPECIFIED

- LEADS TO BE LOCATED WITHIN .007 IN/ 0.18 mm OF THEIR TRUE POSITIONS RELATIVE TO A MAXIMUM WIDTH TAB.
- STANDARD METAL CAN TYPE: SOLID BASE.
- APPLIES TO MIL-AERO AND LINEAR PRODUCTS.
- REFERENCE JEDEC REGISTRATION TO-46, JEDEC PUBLICATION No. 95.

APPROVALS	DATE	BY
DRW: T. LEQUANG	05/04/1994	
ENGR. CHK:		
ENGR. CHK:		
PROJECTION		
SCALE	N/A	REV
SIZE	C	(SC)MKT-H02A
DO NOT SCALE DRAWING		
SHEET 1 of 1		

National Semiconductor
2800 Semiconductor Dr., Santa Clara, CA 95052-8090

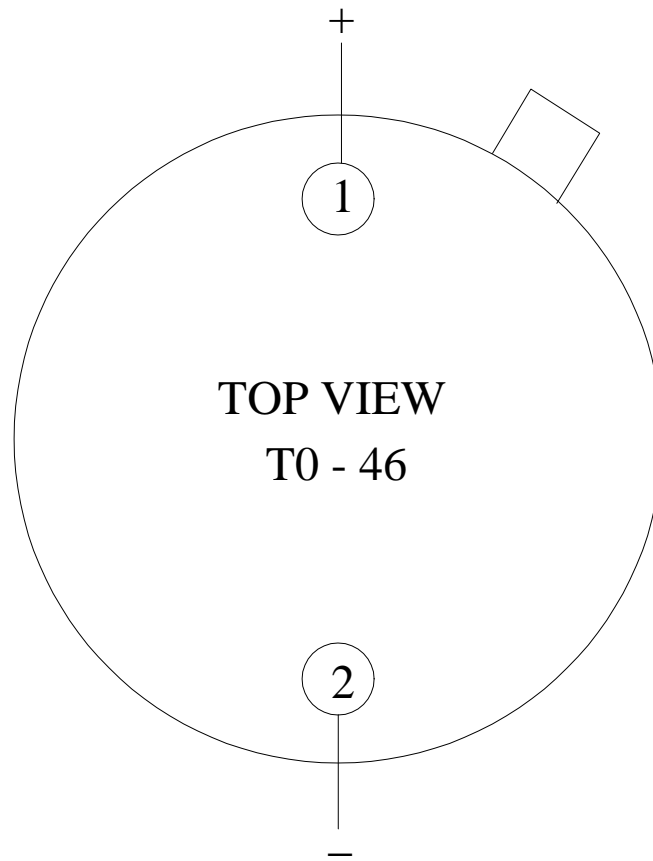
METAL CAN
TO-46, 2 LEAD,
.100 DIA P.C.



LM113WG
10 - LEAD CERPACK SOIC
CONNECTION DIAGRAM
TOP VIEW
P000472A



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2900 SEMICONDUCTOR DRIVE
SANTA CLARA, CA 95050



LM103H, LM113H, LM129H
2 - LEAD TO-46
CONNECTION DIAGRAM
TOP VIEW
P000475A



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2900 SEMICONDUCTOR DRIVE
SANTA CLARA, CA 95050

Revision History

Rev	ECN #	Rel Date	Originator	Changes
2A1	M0004007	06/03/02	Rose Malone	Update MDS: MNLM113-1-X, Rev. 1A0 to 2A1. Update Main Table, Features Section, Absolute Section, Notes Section and Graphics Sections.